

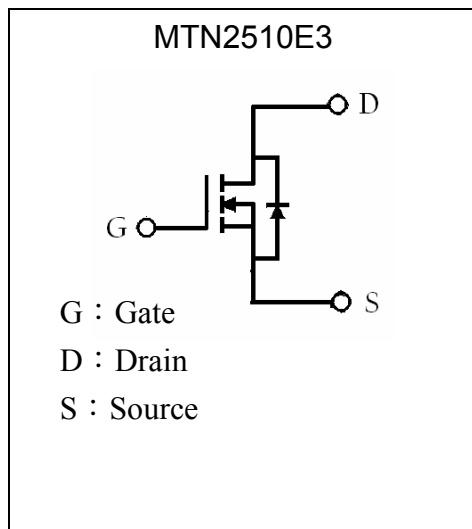
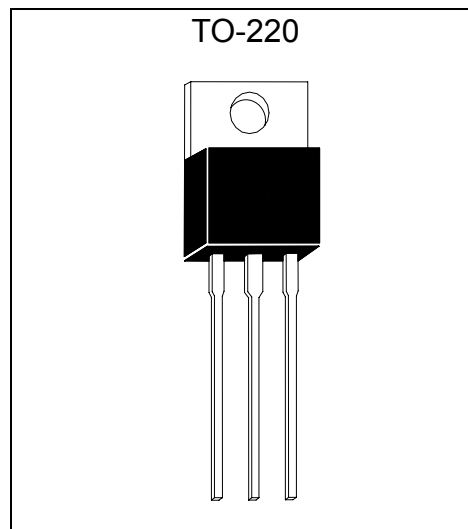
N-Channel Enhancement Mode Power MOSFET

MTN2510E3

BV_{DSS}	100V
I_D	50A
$R_{DS(on)(TYP)} @ V_{GS}=10V, I_D=30A$	17m Ω

Features

- Low Gate Charge
- Simple Drive Requirement
- Repetitive Avalanche Rated
- Fast Switching Characteristic
- RoHS compliant package

Symbol

Outline

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Limits	Unit	
Drain-Source Voltage	V_{DS}	100	V	
Gate-Source Voltage	V_{GS}	± 30		
Continuous Drain Current @ $T_C=25^\circ\text{C}$	I_D	50	A	
Continuous Drain Current @ $T_C=100^\circ\text{C}$	I_D	35		
Pulsed Drain Current (Note 1)	I_{DM}	150		
Avalanche Current	I_{AS}	30		
Avalanche Energy @ $L=0.1\text{mH}, I_D=30\text{A}, R_G=25\Omega$	E_{AS}	45	mJ	
Repetitive Avalanche Energy @ $L=0.05\text{mH}$ (Note 2)	E_{AR}	22.5		
Power Dissipation	$T_C=25^\circ\text{C}$	P_D	155	W
	$T_C=100^\circ\text{C}$		61	
Operating Junction and Storage Temperature		T_j, T_{stg}	-55~+175	$^\circ\text{C}$

Note : 1. Pulse width limited by maximum junction temperature
2. Duty cycle $\leq 1\%$



Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	R _{th,j-c}	0.97	°C/W
Thermal Resistance, Junction-to-ambient, max	R _{th,j-a}	62.5	°C/W

Characteristics (T_c=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	100	-	-	V	V _{GS} =0V, I _D =250μA
V _{GS(th)}	1.5	2.4	4.0	V	V _{DS} = V _{GS} , I _D =250μA
G _{FS}	-	38	-	S	V _{DS} =5V, I _D =30A
I _{GSS}	-	-	±100	nA	V _{GS} =±30
I _{DSS}	-	-	1	μA	V _{DS} =80V, V _{GS} =0V
	-	-	25	μA	V _{DS} =70V, V _{GS} =0V, T _j =125°C
*R _{DS(ON)}	-	17	30	mΩ	V _{GS} =10V, I _D =30A
*I _{D(ON)}	50	-	-	A	V _{DS} =10V, V _{GS} =10V
Dynamic					
*Q _g	-	25	-	nC	I _D =30A, V _{DS} =50V, V _{GS} =10V
*Q _{gs}	-	6.1	-		
*Q _{gd}	-	9.2	-		
*t _{d(ON)}	-	19	-	ns	V _{DS} =50V, I _D =1A, V _{GS} =10V, R _G =6Ω
*t _r	-	67	-		
*t _{d(OFF)}	-	75	-		
*t _f	-	34	-		
C _{iss}	-	1888	-	pF	V _{GS} =0V, V _{DS} =25V, f=1MHz
C _{oss}	-	236	-		
C _{rss}	-	124	-		
R _g	-	2	-	Ω	V _{GS} =15mV, V _{DS} =0V, f=1MHz
Source-Drain Diode					
*I _S	-	-	50	A	
*I _{SM}	-	-	150		
*V _{SD}	-	0.88	1.3	V	I _F =I _S , V _{GS} =0V
*t _{rr}	-	120	-	ns	I _F =25A, V _{GS} =0, dI/dt=100A/μs
*Q _{rr}	-	380	-	nC	

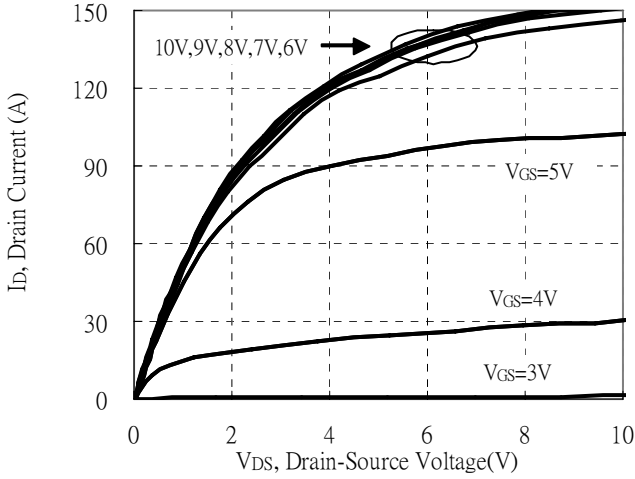
*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

Ordering Information

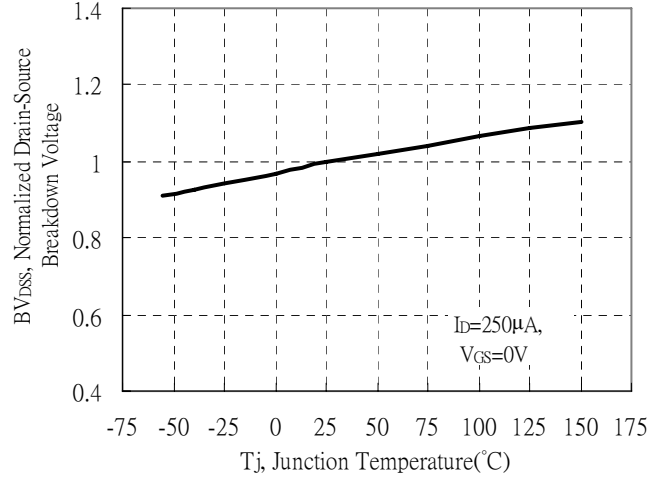
Device	Package	Shipping
MTN2510E3-0-UB-S	TO-220 (Pb-free lead plating package)	50 pcs/tube, 20 tubes/box, 4 boxes / carton

Typical Characteristics

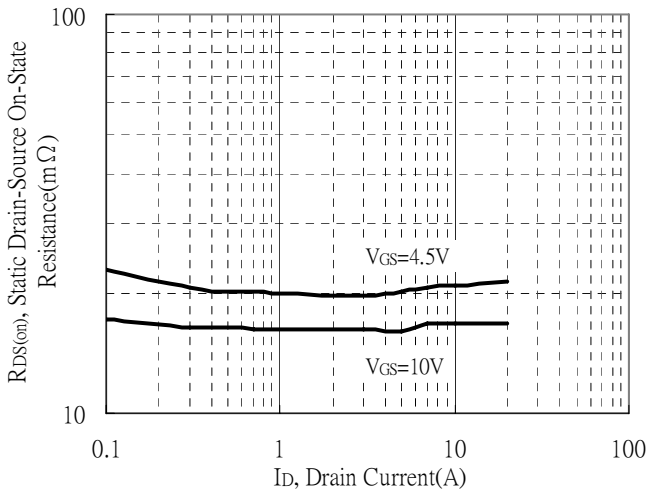
Typical Output Characteristics



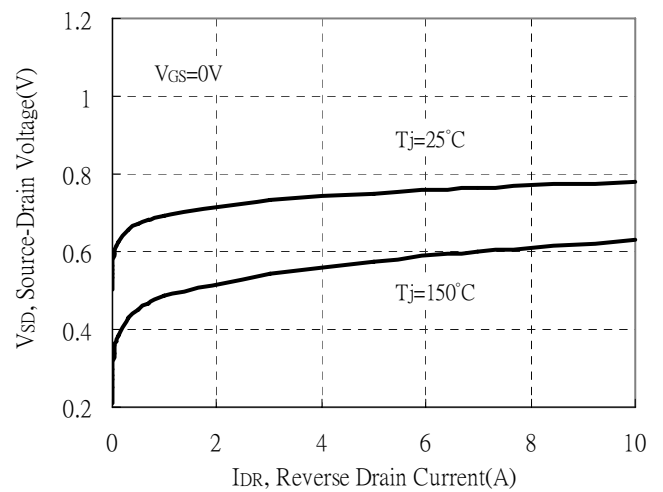
Brekdown Voltage vs Ambient Temperature



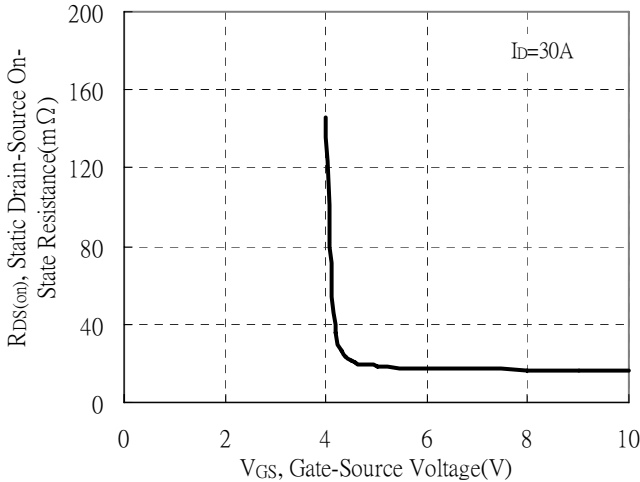
Static Drain-Source On-State resistance vs Drain Current



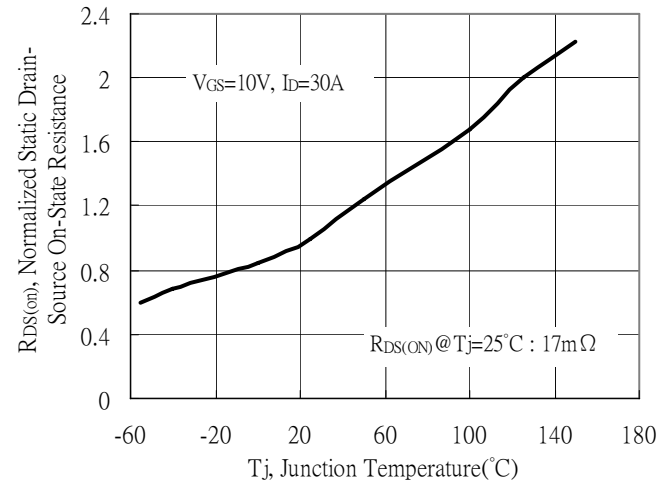
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

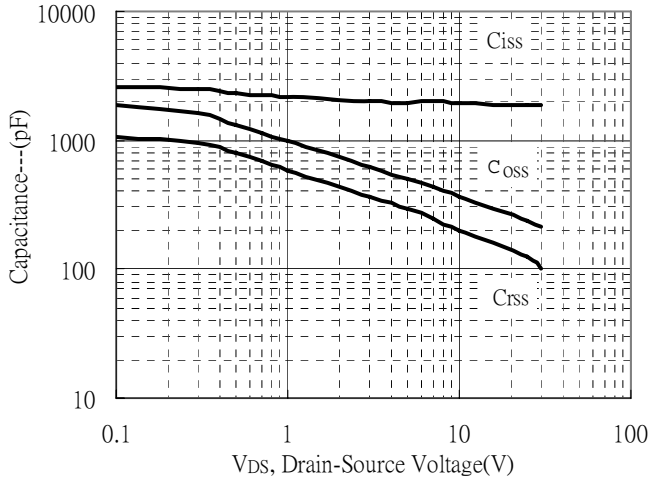


Drain-Source On-State Resistance vs Junction Temperature

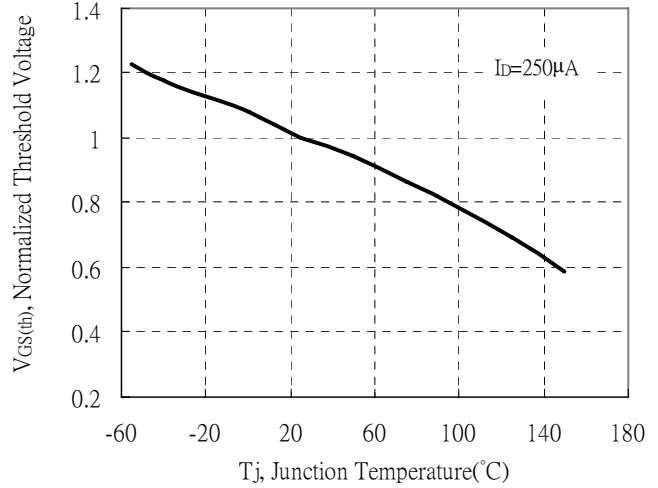


Typical Characteristics(Cont.)

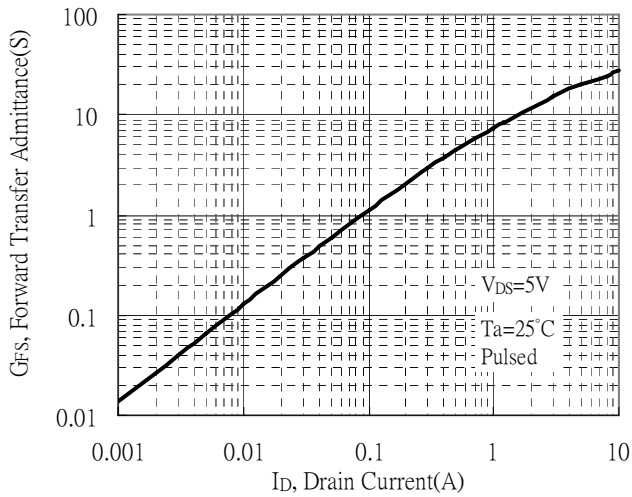
Capacitance vs Drain-to-Source Voltage



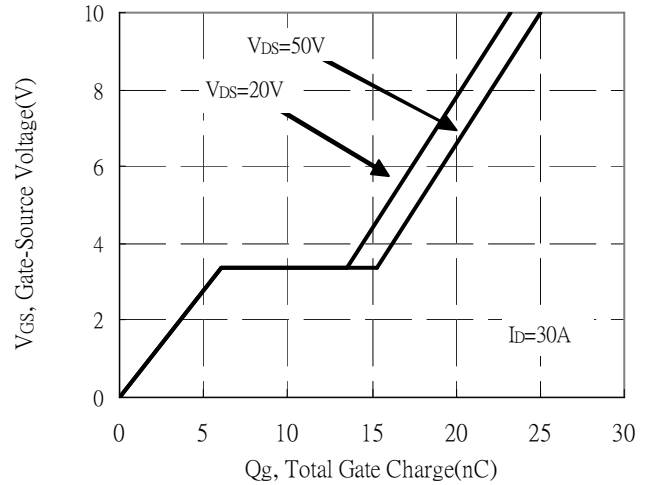
Threshold Voltage vs Junction Temperature



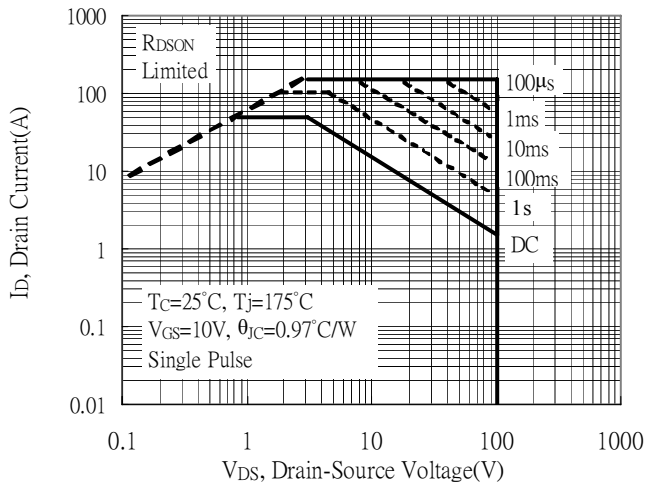
Forward Transfer Admittance vs Drain Current



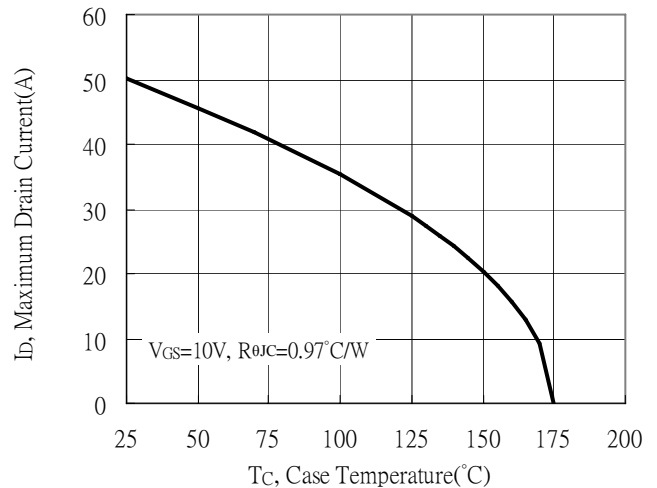
Gate Charge Characteristics



Maximum Safe Operating Area



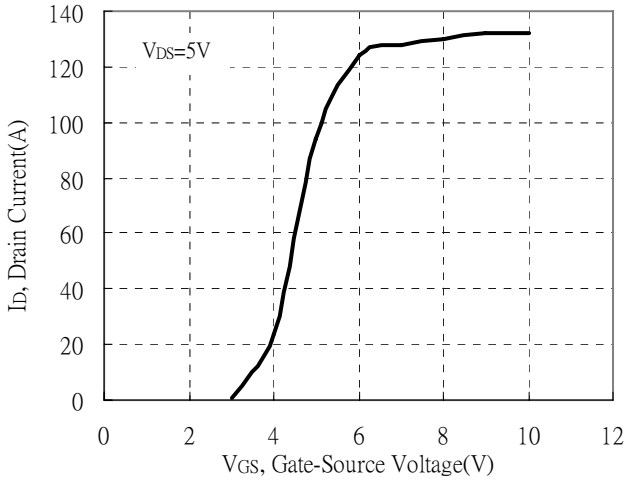
Maximum Drain Current vs Case Temperature



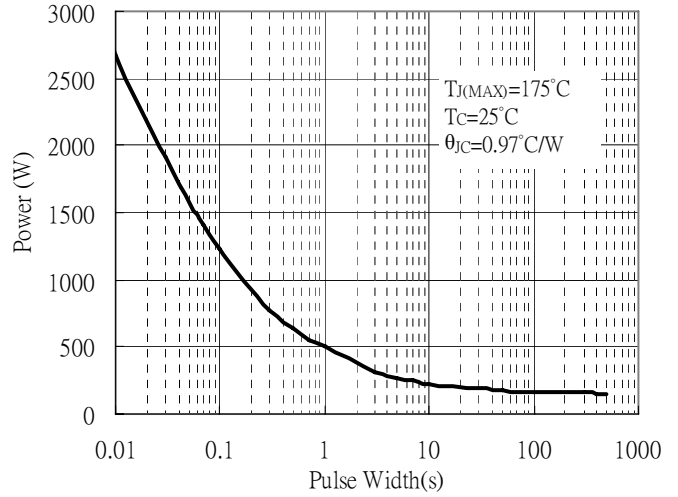


Typical Characteristics(Cont.)

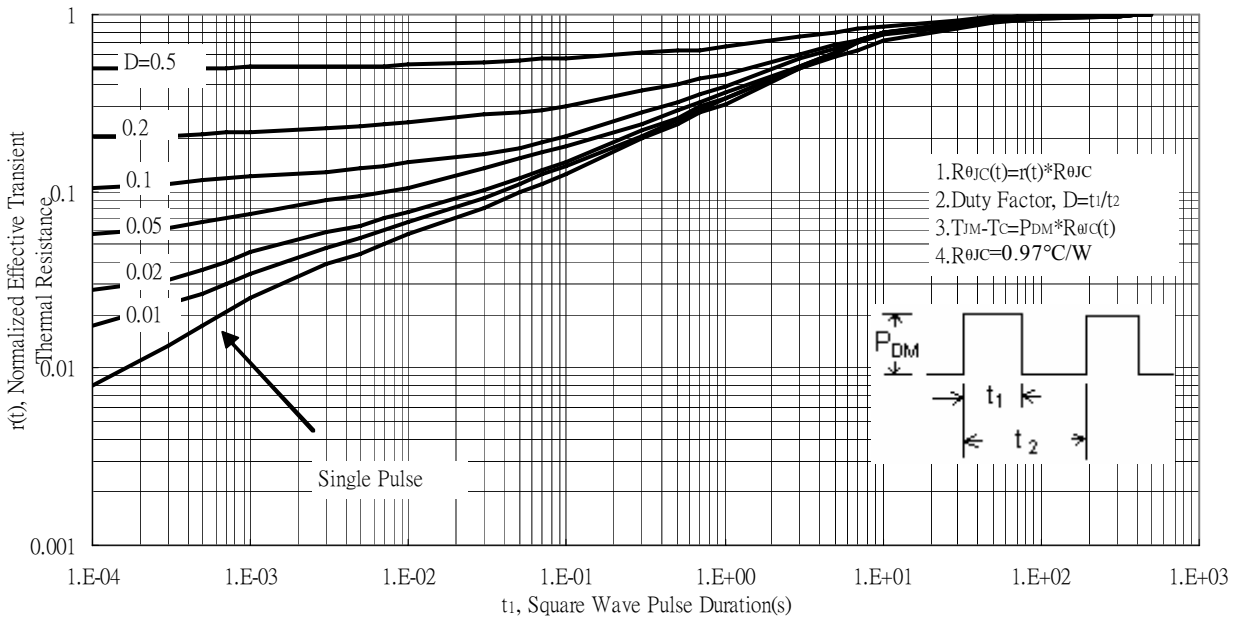
Typical Transfer Characteristics



Single Pulse Maximum Power Dissipation

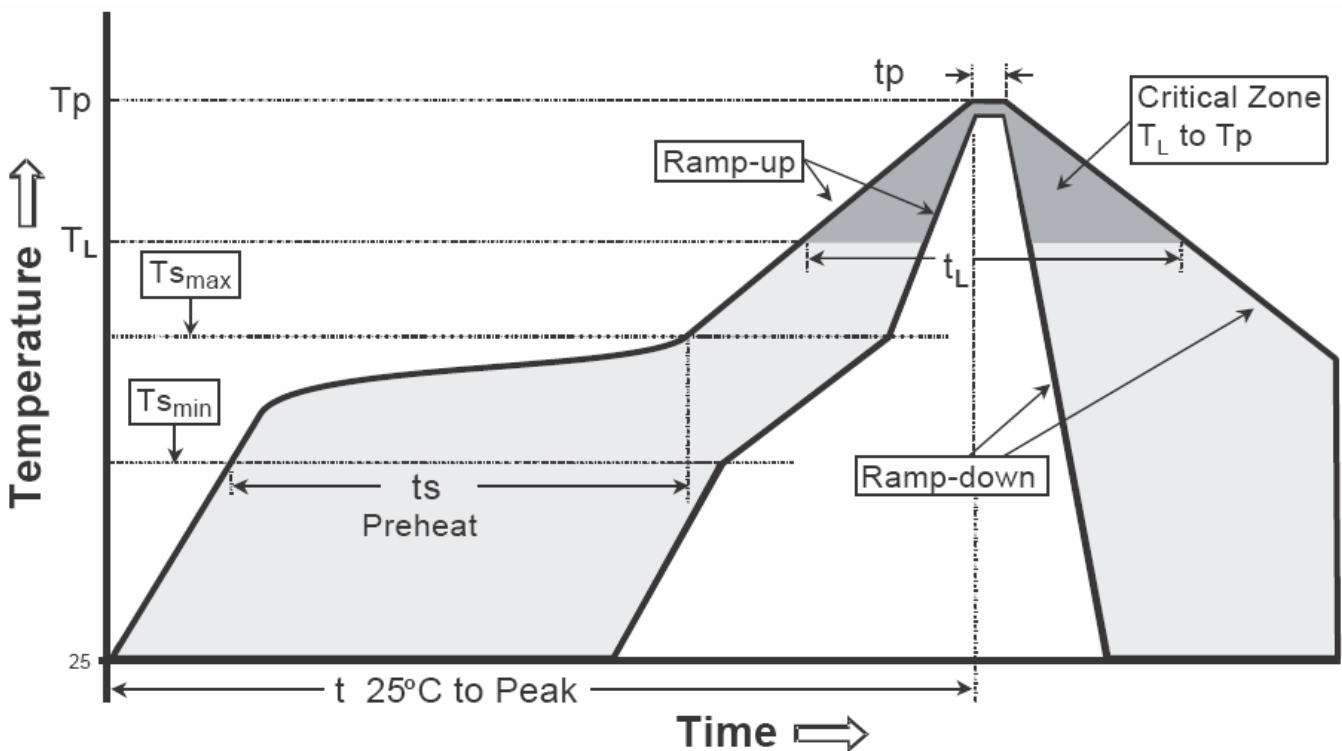


Transient Thermal Response Curves



Recommended wave soldering condition

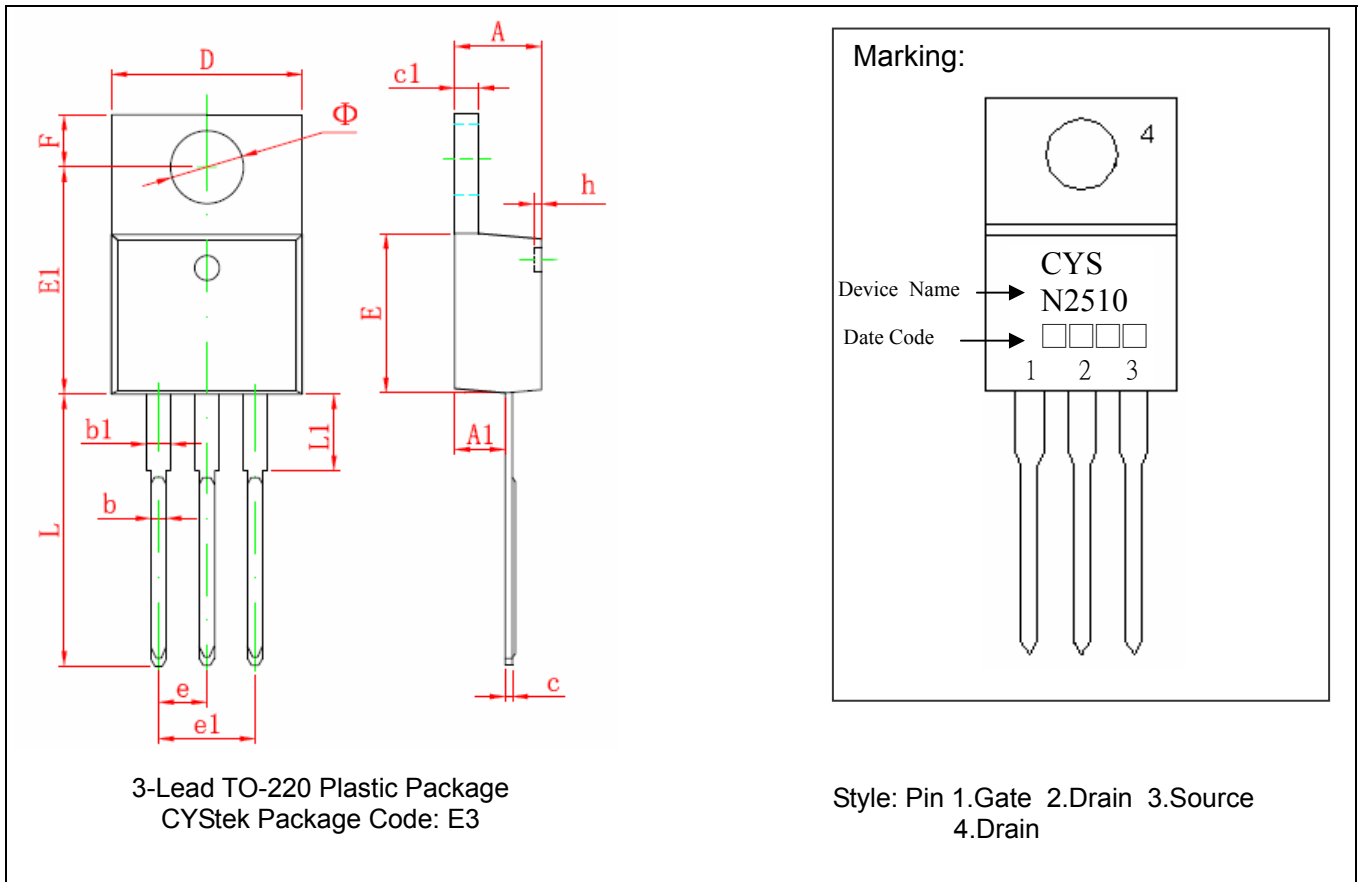
Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow


Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-220 Dimension



*: Typical

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184	E1	12.060	12.460	0.475	0.491
A1	2.520	2.820	0.099	0.111	e	2.540*		0.100*	
b	0.710	0.910	0.028	0.036	e1	4.980	5.180	0.196	0.204
b1	1.170	1.370	0.046	0.054	F	2.590	2.890	0.102	0.114
c	0.310	0.530	0.012	0.021	h	0.000	0.300	0.000	0.012
c1	1.170	1.370	0.046	0.054	L	13.400	13.800	0.528	0.543
D	10.010	10.310	0.394	0.406	L1	3.560	3.960	0.140	0.156
E	8.500	8.900	0.335	0.350	Φ	3.735	3.935	0.147	0.155

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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